

In the Claims:

1. (Withdrawn)
2. (Withdrawn)
3. (Withdrawn)
4. (Withdrawn)
5. (Withdrawn)
6. (Withdrawn)
7. (Withdrawn)
8. (Withdrawn)
9. (Withdrawn)
10. (Withdrawn)
11. (Withdrawn)
12. (Withdrawn)
13. (Cancelled)
14. (Currently amended) The method of Claim 13, wherein ~~said mask~~ the metallic layer includes ~~comprises a~~ platinum line.
15. (Cancelled)
16. (Currently amended) The method of Claim 13, wherein ~~said thin wall~~ the distance between the sidewalls is between 80 and 200 nanometers ~~thick~~.
17. (New) An integrated sample holder for a TEM sample, comprising

a base of a semiconductor material, having a top surface, a substantially flat bottom surface area sized to engage a TEM double tilt holder,

a TEM sample, extending upward from the base, having an upper surface and opposing, substantially parallel sidewalls, and

a metallic layer disposed on the upper surface.

18. (New) The integrated sample holder of claim 17, further comprising an elongated notch at the top surface of the base running substantially parallel to an edge of the base.
19. (New) The integrated sample holder of claim 17, in which the metallic layer covers substantially the entire upper surface.
20. (New) The integrated sample holder of claim 17, in which the TEM sample includes a layer of insulating material.